

Description

The AO4818 uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



General Features SOP-8

V_{DS} = 30V I_D = 8.5 A

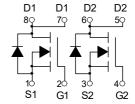
 $R_{DS(ON)} < 18m\Omega$ @ $V_{GS}=4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply



Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AO4818	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

	5	- ,	
Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _G S	Gate-Source Voltage	<u>+</u> 20	V
ID@TA=25°C	Drain Current, V _{GS} @ 4.5V ³	8.5	А
I _D @T _A =70°C	Drain Current, V _{GS} @ 4.5V ³	5.8	Α
Ірм	Pulsed Drain Current ¹	37	А
PD@TA=25°C	Total Power Dissipation	1.5	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient ³	85	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA		0.034		V/°C	
Б	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =7A	-	15	18	mΩ	
R _{DS(ON)}	Static Dialii-Source Off-Nesistance	V _{GS} =4.5V , I _D =4A		22	28		
$V_{GS(th)}$	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2		2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS , ID -230UA	1	-5.8		mV/°C	
	Drain-Source Leakage Current	V_{DS} =24V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1		
I _{DSS}		V_{DS} =24V , V_{GS} =0V , T_J =55 $^{\circ}$ C			5	uA	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =7A		6		S	
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.5		Ω	
Qg	Total Gate Charge (4.5V)			6			
Q _{gs}	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =7A		2.5		nC	
Q _{gd}	Gate-Drain Charge			2.1			
T _{d(on)}	Turn-On Delay Time			2.4		ns	
Tr	Rise Time	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω		7.8			
T _{d(off)}	Turn-Off Delay Time	I _D =7A		22			
T _f	Fall Time			4			
C _{iss}	Input Capacitance			572			
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		80		pF	
C _{rss}	Reverse Transfer Capacitance			65			
Is	Continuous Source Current ^{1,5}	V V 0V 5 0			7.3	Α	
I _{SM}	Pulsed Source Current ^{2,5}	──V _G =V _D =0V , Force Current			37	Α	
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V	
t _{rr}	Reverse Recovery Time			20		nS	
Q _{rr}	Reverse Recovery Charge	IF=7A,dI/dt=100A/µs,T _J =25°C		1.1		nC	

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V,L=0.1mH, I_{AS} =21A
- 4. The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

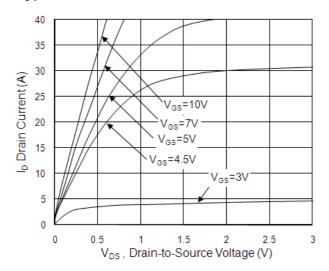


Fig.1 Typical Output Characteristics

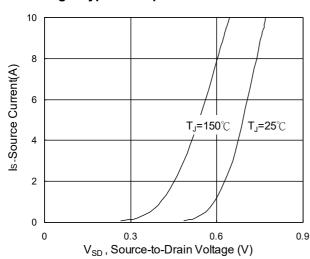


Fig.3 Forward Characteristics Of Reverse

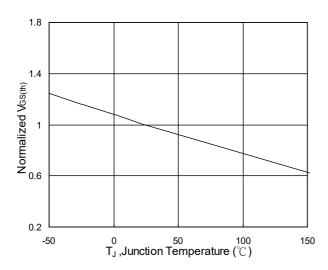


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

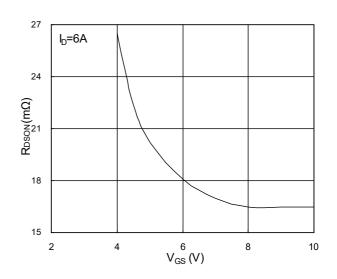


Fig.2 On-Resistance vs. G-S Voltage

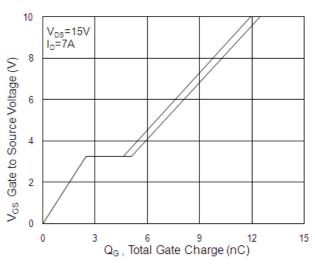


Fig.4 Gate-Charge Characteristics

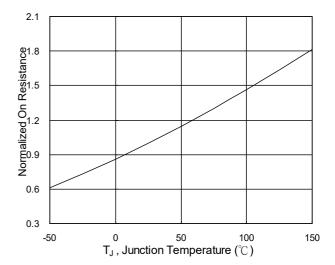
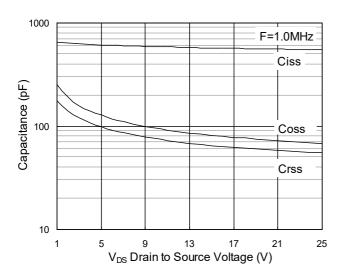


Fig.6 Normalized R_{DSON} vs. T_J



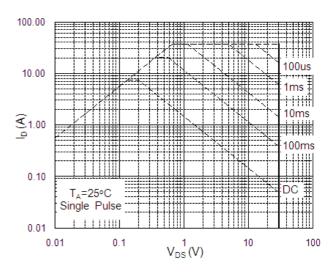


Fig.7 Capacitance

Fig.8 Safe Operating Area

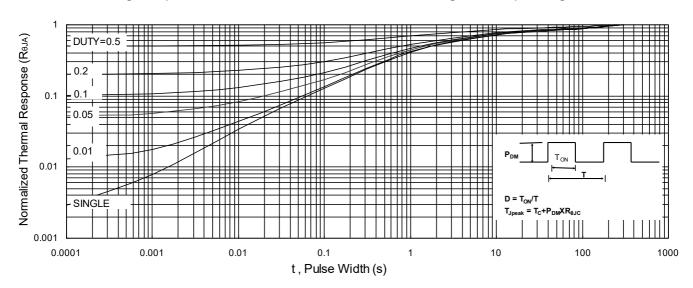


Fig.9 Normalized Maximum Transient Thermal Impedance

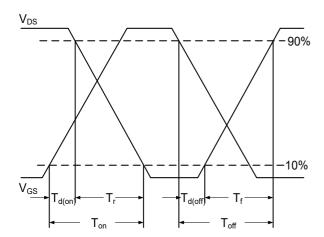


Fig.10 Switching Time Waveform

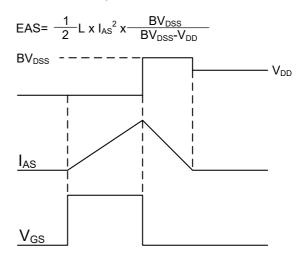
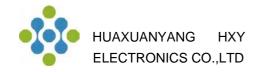
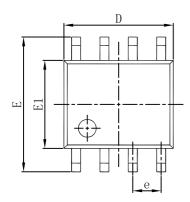
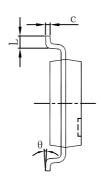


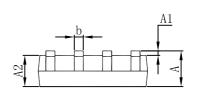
Fig.11 Unclamped Inductive Switching Waveform



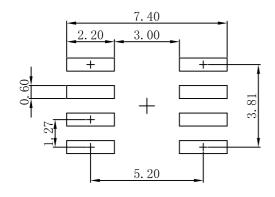
SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	1. 350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6. 200	0. 228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note: 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

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